

☐ **Applications**

- Low noise amplifier, oscillator and buffer amplifier up to 3 GHz

☐ **Features**

- High gain bandwidth product

$$f_T = 16 \text{ GHz @ } V_{CE} = 2 \text{ V, } I_C = 50 \text{ mA}$$

$$f_T = 18 \text{ GHz @ } V_{CE} = 3 \text{ V, } I_C = 70 \text{ mA}$$

- High power gain

$$|S_{21}|^2 = 12 \text{ dB @ } V_{CE} = 2 \text{ V, } I_C = 50 \text{ mA, } f = 1.8 \text{ GHz}$$

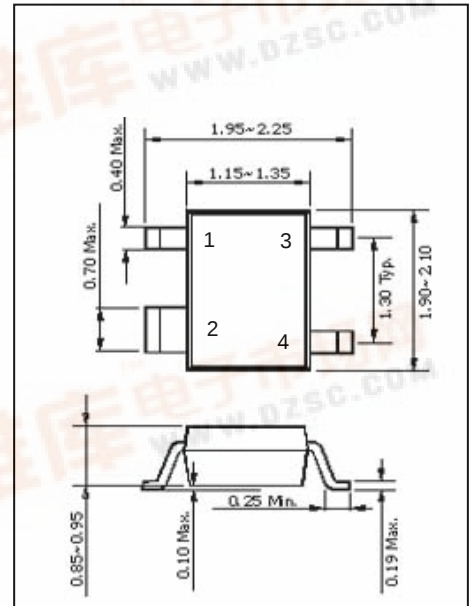
$$\text{MAG} = 14 \text{ dB @ } V_{CE} = 2 \text{ V, } I_C = 50 \text{ mA, } f = 1.8 \text{ GHz}$$

- Low noise figure

$$\text{NF} = 1.5 \text{ dB @ } V_{CE} = 2 \text{ V, } I_C = 7 \text{ mA, } f = 1.8 \text{ GHz}$$

SOT-343

Unit in mm

**Pin Configuration**

1. Base
2. Emitter
3. Emitter
4. Collector

☐ **Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)**

Parameter	Symbol	Ratings	Unit
Collector to Base Breakdown Voltage	BV_{CBO}	10	V
Collector to Emitter Breakdown Voltage	BV_{CEO}	4.5	V
Emitter to Base Breakdown Voltage	BV_{EBO}	1.5	V
Collector Current	I_C	100	mA
Total Power Dissipation	P_{tot}	450	mW
Operating Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 ~ 150	$^\circ\text{C}$

Caution : Electro Static Discharge sensitive device

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□ **Electrical Characteristics** ($T_A = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB} = 7\text{ V}, I_E = 0\text{ mA}$	-	-	1.0	μA
	I_{CEO}	$V_{CE} = 2\text{ V}, I_B = 0\text{ mA}$	-	-	1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0\text{ mA}$	-	-	0.5	μA
DC Current Gain	h_{FE}	$V_{CE} = 3\text{ V}, I_C = 5\text{ mA}$	50	-	260	
Gain Bandwidth Product	f_T	$V_{CE} = 2\text{ V}, I_C = 50\text{ mA}$	14	16	-	GHz
		$V_{CE} = 3\text{ V}, I_C = 70\text{ mA}$	16	18	-	GHz
Maximum Available Gain	MAG	$V_{CE} = 2\text{ V}, I_C = 50\text{ mA}, f = 0.9\text{ GHz}$	20	22	-	dB
		$V_{CE} = 2\text{ V}, I_C = 50\text{ mA}, f = 1.8\text{ GHz}$	12	14	-	dB
Insertion Power Gain	$ S_{21} ^2$	$V_{CE} = 2\text{ V}, I_C = 50\text{ mA}, f = 0.9\text{ GHz}$	16	18	-	dB
		$V_{CE} = 2\text{ V}, I_C = 50\text{ mA}, f = 1.8\text{ GHz}$	10	12	-	dB
Noise Figure	NF	$V_{CE} = 2\text{ V}, I_C = 7\text{ mA}, f = 1.8\text{ GHz}$	-	1.5	2.0	dB
Reverse Transfer Capacitance	C_{re}	$V_{CB} = 2\text{ V}, I_E = 0\text{ mA}, f = 1\text{ MHz}$	-	0.35	-	pF

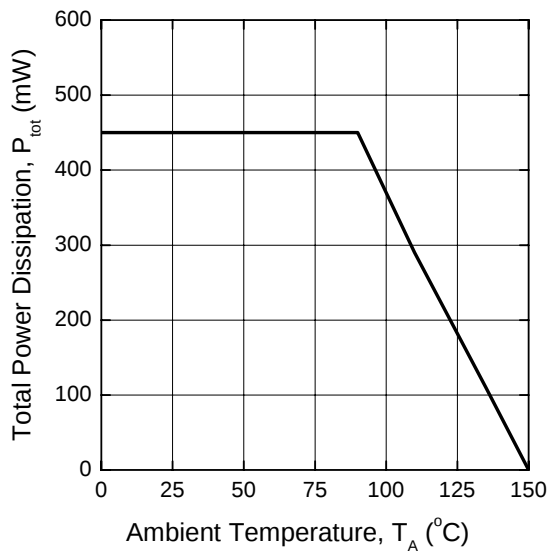
□ **h_{FE} Classification**

Marking	BG1	BG2
h_{FE} Value	50 - 150	130 - 260

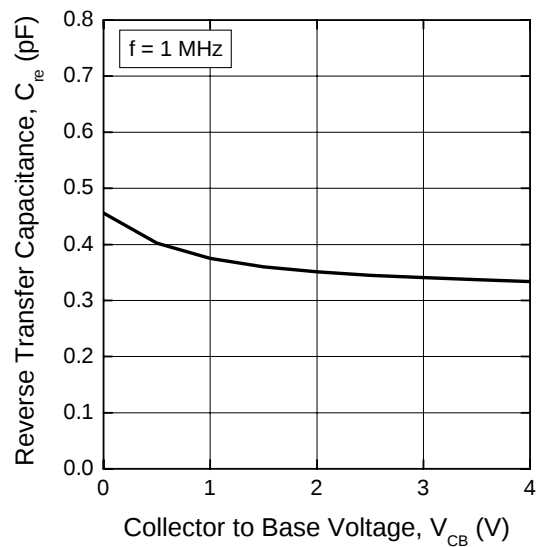
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□ **Typical Characteristics** ($T_A = 25^\circ\text{C}$, unless otherwise specified)

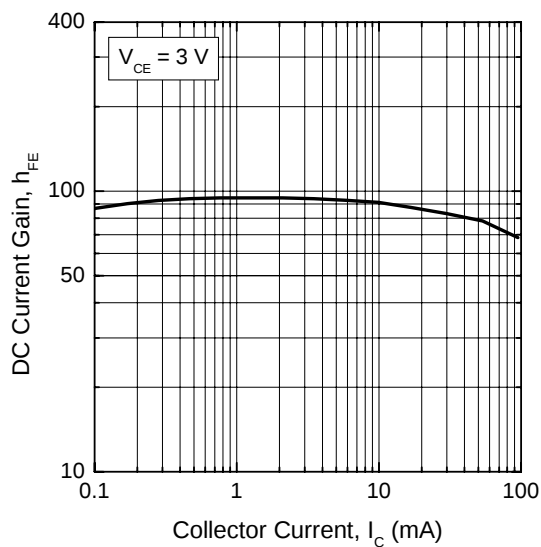
**Total Power Dissipation
vs. Ambient Temperature**



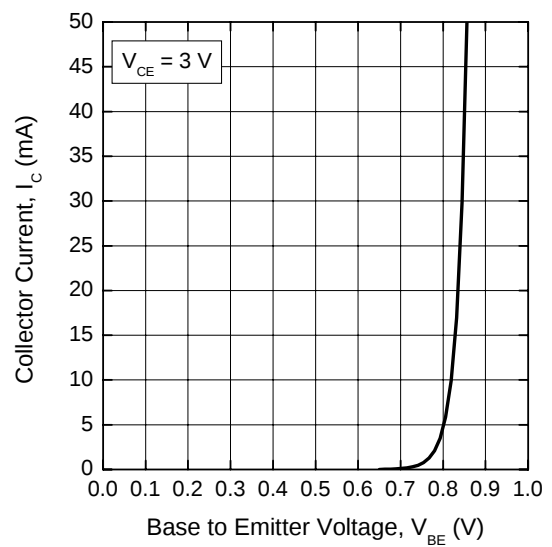
**Reverse Transfer Capacitance
vs. Collector to Base Voltage**



**DC Current Gain
vs. Collector Current**

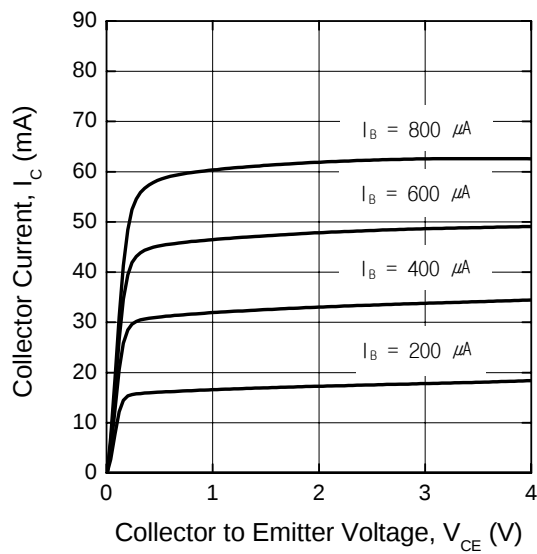


**Collector Current
vs. Base to Emitter Voltage**

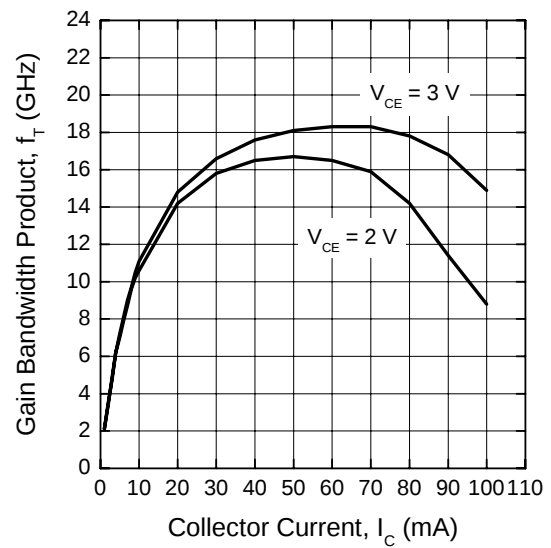


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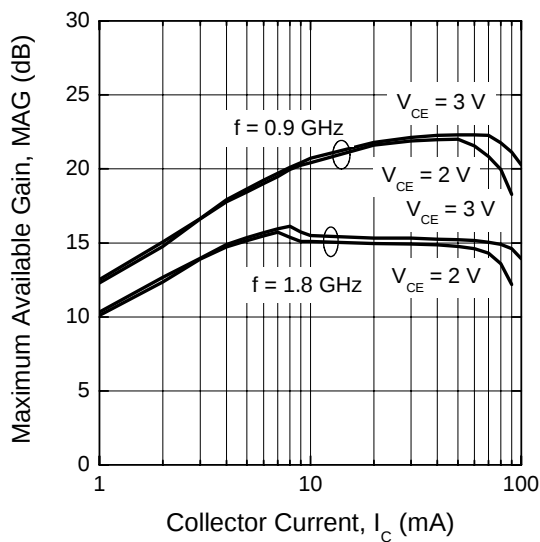
**Collector Current
vs. Collector to Emitter Voltage**



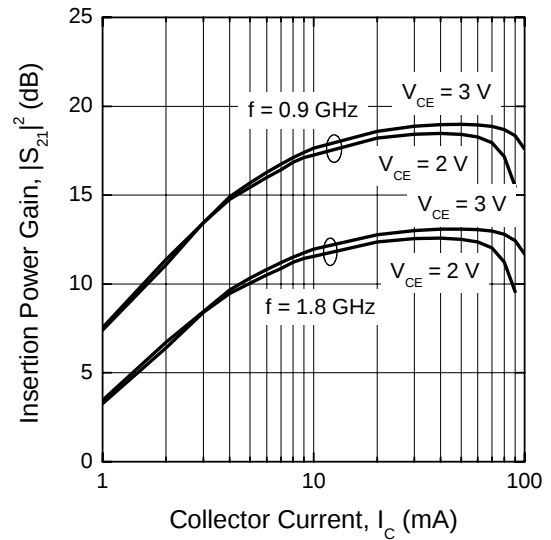
**Gain Bandwidth Product
vs. Collector Current**



**Maximum Available Gain
vs. Collector Current**

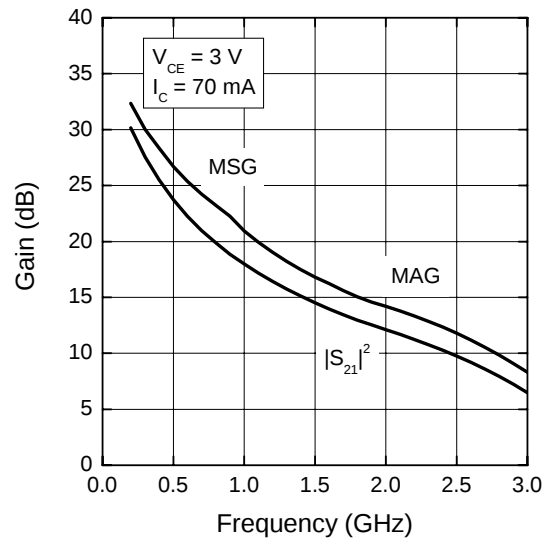
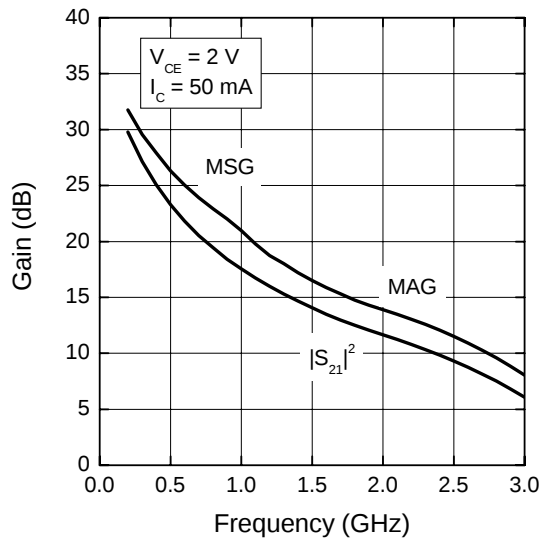


**Insertion Power Gain
vs. Collector Current**



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**Power Gain
vs. Frequency**



**Noise Figure
vs. Collector Current**

at $V_{CE} = 2\text{ V}$, I_C = parameters, $Z_S = Z_{Sopt}$

